HX1009-AMH

Dual High Efficiency PWM Step-Down DC/DC Converter

Features

- Up to 90% Efficiency
- Current Mode Operation for Excellent Line and Load Transient Response
- Low Quiescent Current (one channel):190uA
- Up to 900mA Load Current
- Output Voltage：0.6V～5.5V
- Automatic PWM/PFM Mode Switching
- No Schottky Diode Required
- 1.43MHz Fixed Frequency Switching
- Short-Circuit Protection
- Shutdown Quiescent Current: < 1μA
- DFN3*3-12L Package

Applications

- Digital cameras and MP3
- Palmtop computers / PDAs
- Cellular phones
- Wireless handsets and DSL modems
- PC cards
- Portable media players

Description

The HX1009-AMH is a dual high efficiency synchronous, PWM step-down DC/DC converters working under an input voltage range of 2.5V to 5.5V. This feature makes the HX1009-AMH suitable for single Li-Ion battery-powered applications. 100% duty cycle capability extends battery life in portable devices, while the quiescent current is 190μA with no load, and drops to < 1μA in shutdown.

The internal synchronous switch is desired to increase efficiency without an external Schottky diode. The 1.43 MHz fixed switching frequency allows the using of tiny, low profile inductors and ceramic capacitors, which minimized overall solution footprint.

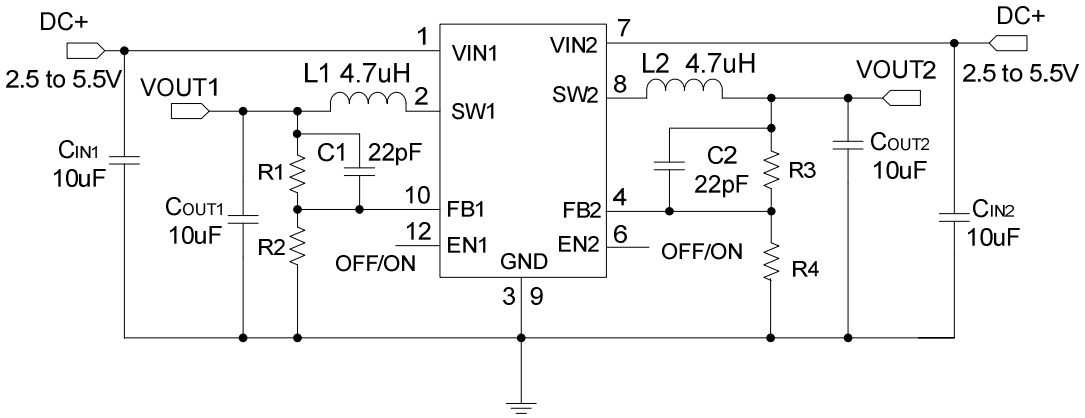
The HX1009-AMH converters are available in the industry standard DFN3*3-12L Packages.

Order Information

HX1009-①②③ :

Symbol	Description
①	Denotes Output voltage: A : Adjustable Output
②	Denotes Package Types: M: DFN3*3-12L
③	H: High Frequency

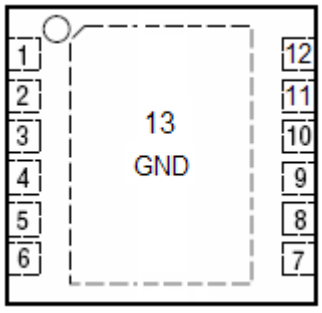
Typical Application Circuit



* $V_{OUT1} = 0.6V \bullet [1 + (R1/R2)]$
* $V_{OUT2} = 0.6V \bullet [1 + (R3/R4)]$

Pin Assignment

TOP VIEW



DFN3*3-12L

PIN Number DFN3*3-12L	PIN Name	Function
1	VIN1	Power Input 1
2	SW1	Switch Node for Output 1
3,9	GND	Ground
4	FB2	Output Feedback Sense for Output 2
5,11	N/C	No Connect
6	EN2	ON/OFF Control (High Enable)
7	VIN2	Power Input 2
8	SW2	Switch Node for Output 2
10	FB1	Output Feedback Sense for Output 1
12	EN1	ON/OFF Control (High Enable)
13	Exposed Pad	Ground

Absolute Maximum Ratings (Note 1)

- Power Dissipation……Internally limited
- $V_{IN1,2}$ ……- 0.3 V ～ + V
- $V_{EN1,2}$ ……- 0.3 V ～ (V_{IN} + 0.3) V
- $V_{SW1,2}$ ……- 0.3 V ～ (V_{IN} + 0.3) V
- $V_{OUT1,2}$……- 0.3 V ～ + 6 V
- $I_{SW1,2}$ ……1.3A
- Operating Temperature Range ……- 40℃ ～ + 85℃
- Lead Temperature (Soldering 10 sec.) ……+ 300℃
- Storage Temperature Range ……- 65℃ ～ + 150℃
- Junction Temperature ……+ 125℃

Note 1. Stresses listed as the above “Absolute Maximum Ratings” may cause permanent damage to the device. These are for stress ratings. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may remain possibility to affect device reliability.

Electrical Characteristics (VOUT1 or VOUT2)

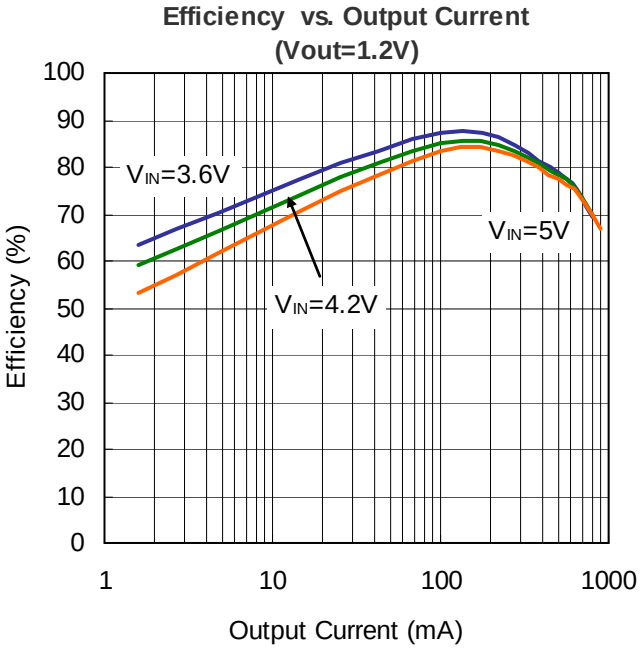
Operating Conditions: TA=25℃, V_{IN}=3.6V unless otherwise specified.

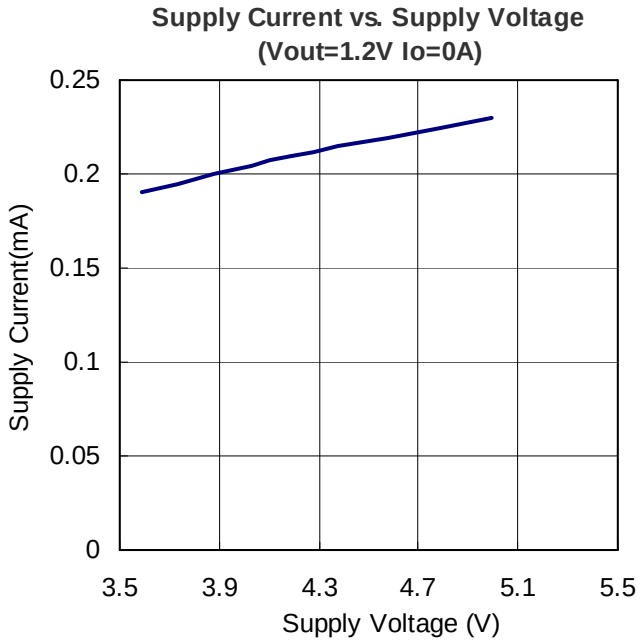
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V_{OUT}	Output Voltage	I_{OUT} = 100mA, R1/R2=2	1.75	1.80	1.85	V
V_{IN}	Operating Voltage Range		2.5		5.5	V
V_{FB}	Regulated Voltage	TA = 25℃	0.5880	0.6	0.6120	V
I_{FB}	Feedback Current				±30	nA
ΔV_{FB}	V_{REF}	V_{IN}=2.5V~5.5V		0.03	0.4	%/V
F_{OSC}	Oscillator Frequency	V_{FB} = 0.6V or V_{OUT} = 100%	1.1	1.43	1.7	MHz
I_Q	Quiescent Current	V_{FB} = 0.5V or V_{OUT} = 90%, I_{LOAD} = 0A		190	300	μA
I_S	Shutdown Current	V_{EN} = 0V, V_{IN} = 5V		0.5	1	μA
I_{PK}	Peak Inductor Current	V_{IN} = 3V, V_{FB} = 0.5V or V_{OUT} = 90%, Duty Cycle < 35%	0.8	0.95	1.1	A
R_{PFET}	$R_{DS(ON)}$ of P-Channel FET	I_{SW} = 100mA		0.3		Ω
R_{NFET}	$R_{DS(ON)}$ of N-Channel FET	I_{SW} = -100mA		0.39		Ω
EFFI*	Efficiency	When connected to ext. components V_{IN}=EN=3.6 V, I_{OUT}=100mA		90		%
ΔV_{OUT}	V_{OUT} Line Regulation	V_{IN}=2.5V~5.5V		0.03	0.3	%/V
$V_{LOADREG}$	V_{OUT} Load Regulation			0.33		%

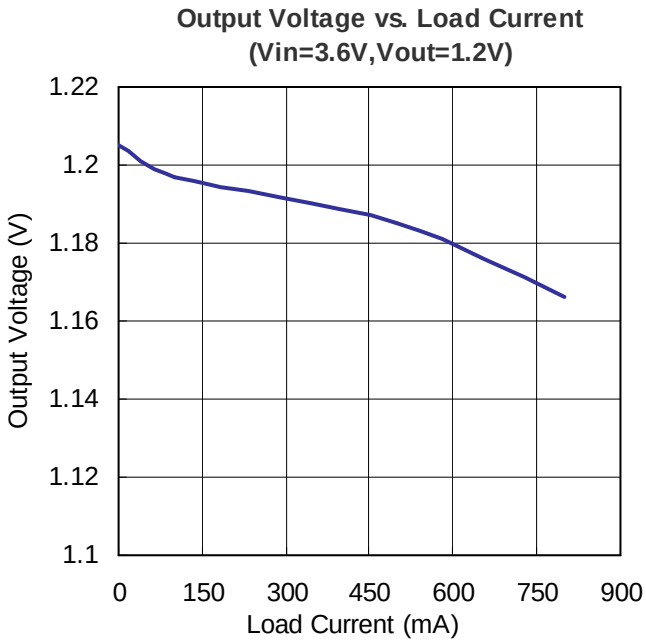
* EFFI = [(Output Voltage × Output Current) / (Input Voltage × Input Current)] × 100%

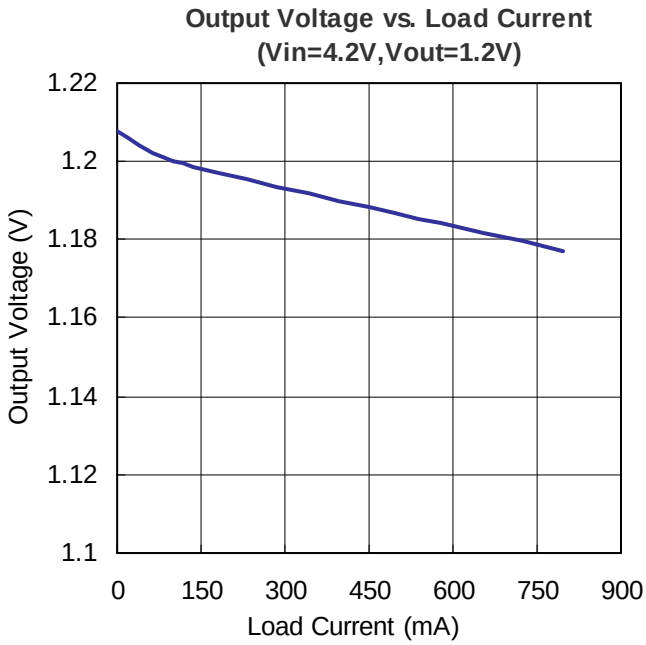
Typical Performance Characteristics (VOUT1 or VOUT2)

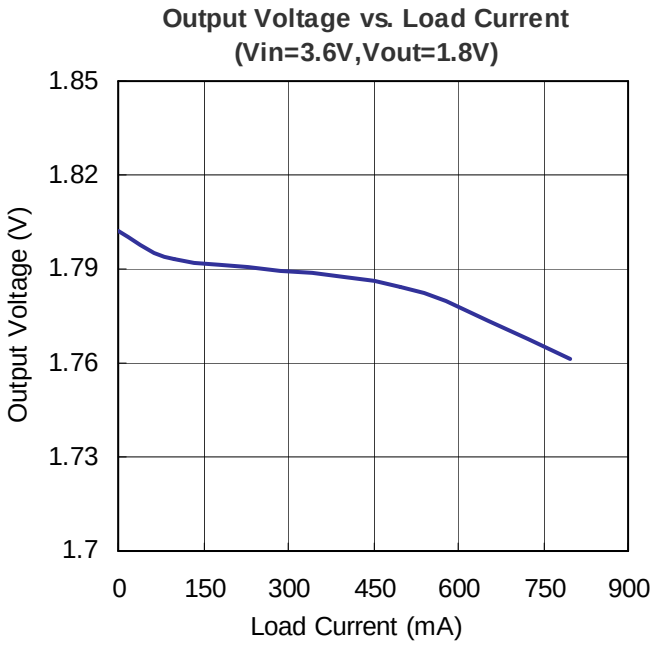
TA=25℃, C_{IN} =10 μF, C_{OUT} =10 μF, L=4.7 μH, unless otherwise noted.

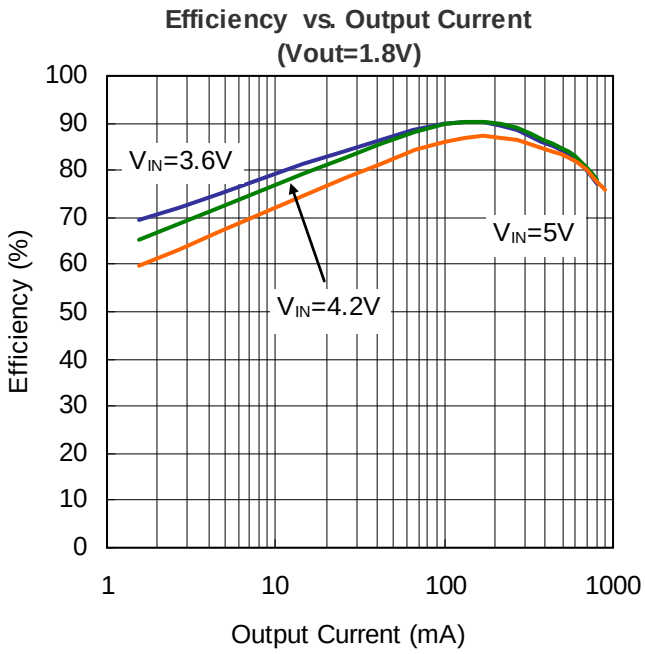


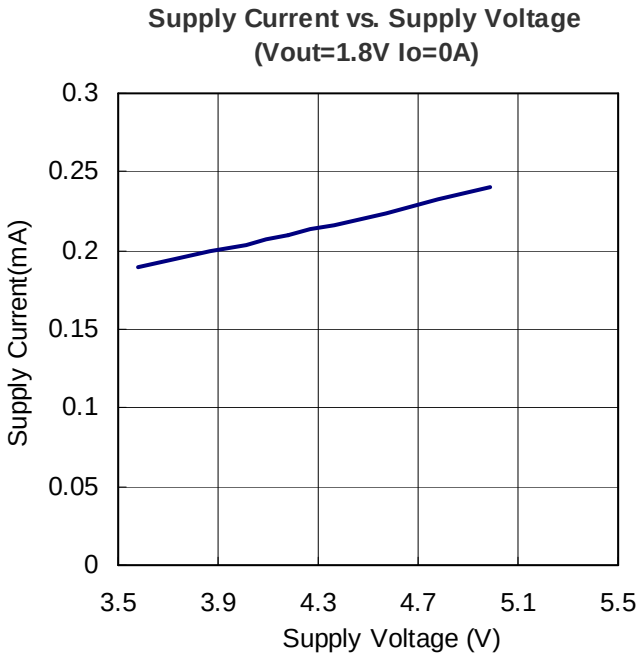


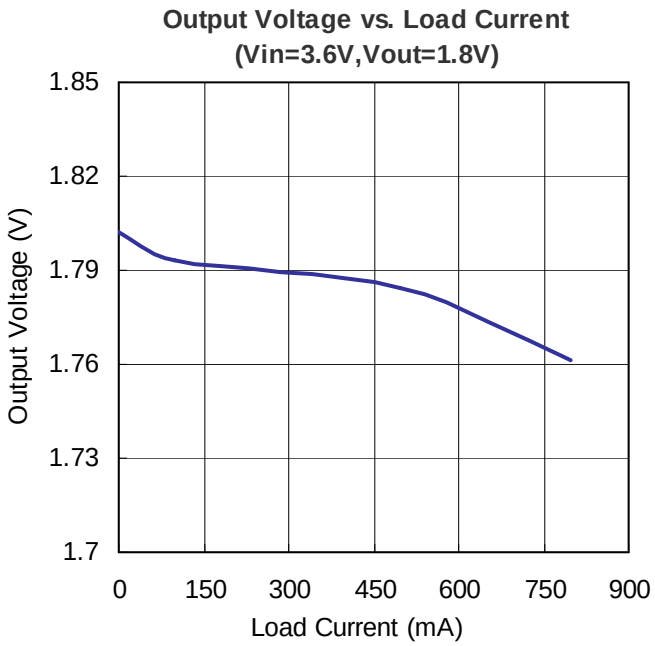





Output Voltage vs. Load Current
(Vin=3.6V,Vout=1.8V)
Output Voltage (V)
1.85
1.82
1.79
1.76
1.73
1.7
0
150
300
450
600
750
900
Load Current (mA)


Efficiency vs. Output Current
(Vout=1.8V)
Efficiency (%)
100
90
80
70
60
50
40
30
20
10
0
VIN=3.6V
VIN=5V
VIN=4.2V
1
10
100
1000
Output Current (mA)


Supply Current vs. Supply Voltage
(Vout=1.8V Io=0A)
Supply Current(mA)
0.3
0.25
0.2
0.15
0.1
0.05
0
3.5
3.9
4.3
4.7
5.1
5.5
Supply Voltage (V)


Output Voltage vs. Load Current
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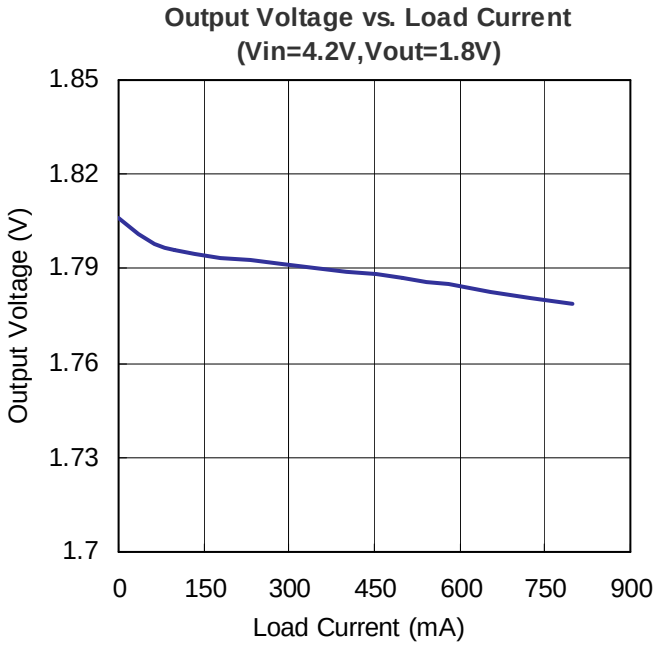
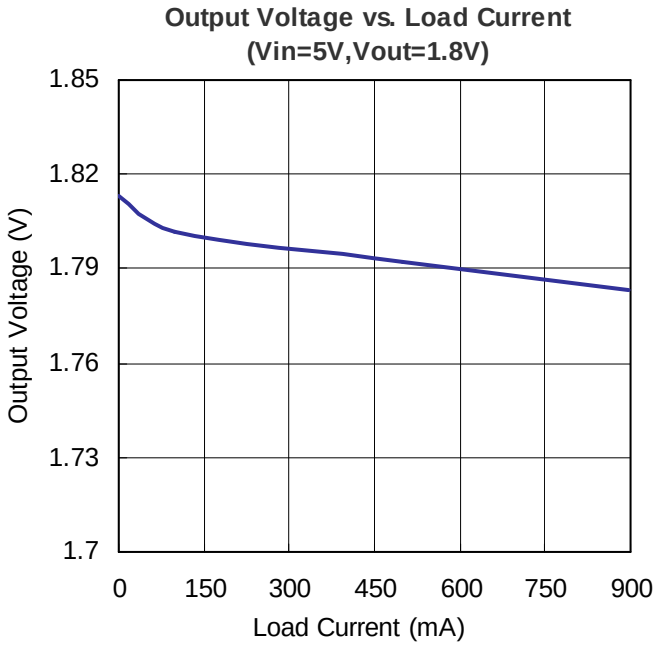
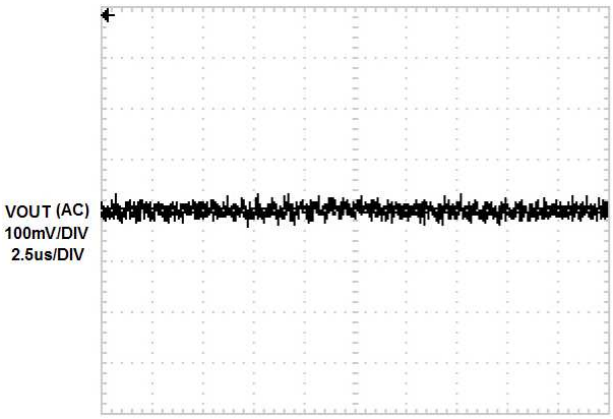
750
900
Load Current (mA)

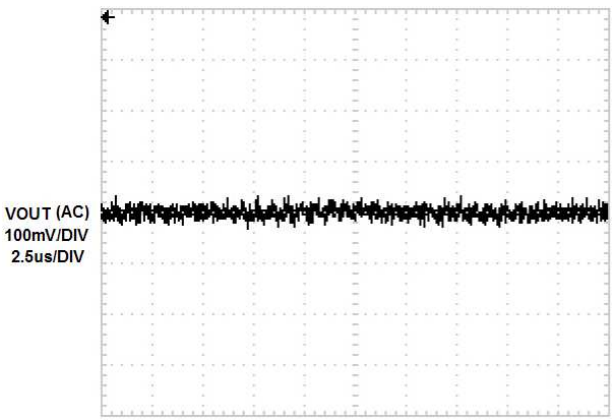




V_{IN}=5V V_{OUT}=1.2V I_{LOAD}=900mA



V_{IN}=5V V_{OUT}=1.8V I_{LOAD}=900mA



PIN DESCRIPTION

VIN1 (Pin 1): Main Supply Pin. Must be closely decoupled to GND, with a 10μF or greater ceramic capacitor.

SW1 (Pin 2): Switch Node for Output 1. This pin connects to the drains of the internal main and synchronous power MOSFET switches.

GND (Pin 3, 9): Ground Pin.

FB2 (Pin 4): Feedback Pin. Receives the feedback voltage from an external resistive divider across the output. The output voltage is set by a resistive divider according to the following formula: V_{OUT2} = 0.6V • [1 + (R3/R4)].

N/C (Pin 5, 11): No Connect.

EN2 (Pin 6): En Control Input. Forcing this pin above 0.9V enables VOUT2. Forcing this pin below 0.6V shutdown VOUT2. In shutdown, all functions are disabled drawing <1μA supply current. Do not leave EN2 floating.

VIN2 (Pin 7): Main Supply Pin. Must be closely decoupled to GND, with a 10μF or greater ceramic capacitor.

SW2 (Pin 8): Switch Node for Output 2. This pin connects to the drains of the internal main and synchronous power MOSFET switches.

FB1 (Pin 10): Feedback Pin. Receives the feedback voltage from an external resistive divider across the output. In the adjustable version, the output voltage is set by a resistive divider according to the following formula: V_{OUT1} = 0.6V • [1 + (R1/R2)].

EN1 (Pin 12): En Control Input. Forcing this pin above 0.9V enables VOUT1. Forcing this pin below 0.6V shutdown VOUT1. In shutdown, all functions are disabled drawing <1μA supply current. Do not leave EN1 floating.

Exposed Pad (Pin13): Ground. Must be soldered to PCB for electrical connection and thermal performance.

Application Information

Inductor Selection

For most applications, the value of the inductor will fall in the range of 1µH to 4.7µH. Its value is chosen based on the desired ripple current. Large value inductors lower ripple current and small value inductors result in higher ripple currents. Higher V_{IN} or V_{OUT} also increases the ripple current as shown in equation .A reasonable starting point for setting ripple current is $\triangle I_L$ = 360mA (40% of 900mA).

$$\Delta I_L = \frac{1}{(f)(L)} V_{OUT}\left(1 - \frac{V_{OUT}}{V_{IN}}\right)$$

The DC current rating of the inductor should be at least equal to the maximum load current plus half the ripple current to prevent core saturation. Thus, a 1.08A rated inductor should be enough for most applications (900mA + 180mA). For better efficiency, choose a low DC-resistance inductor.

Different core materials and shapes will change the size/current and price/current relationship of an inductor. Toroid or shielded pot cores in ferrite or perm alloy materials are small and don't radiate much energy, but generally cost more than powdered iron core inductors with similar electrical characteristics. The choice of which style inductor to use often depends more on the price vs. size requirements and any radiated field/EMI requirements than on what HX1009-AMH requires to operate.

Output and Input Capacitor Selection

In continuous mode, the source current of the top MOSFET is a square wave of duty cycle V_{OUT}/V_{IN}. To prevent large voltage transients, a low ESR input capacitor sized for the maximum RMS current must be used. The maximum RMS capacitor current is given by:

$$C_{IN} \text{ required } I_{RMS} \cong I_{OMAX} \frac{\left[V_{OUT}(V_{IN} - V_{OUT})\right]^{1/2}}{V_{IN}}$$

This formula has a maximum at $V_{IN} = 2V_{OUT}$, where $I_{RMS} = I_{OUT}/2$. This simple worst-case condition is commonly used for design because even significant deviations do not offer much relief. Note that the capacitor manufacturer's ripple current ratings are often based on 2000 hours of life. This makes it advisable to further derate the capacitor, or choose a capacitor rated at a higher temperature than required. Always consult the manufacturer if there is any question.

The selection of C_{OUT} is driven by the required effective series resistance (ESR).Typically, once the ESR requirement for C_{OUT} has been met, the RMS current rating generally far exceeds the $I_{RIPPLE(P-P)}$ requirement. The output ripple ΔV_{OUT} is determined by:

$$\Delta V_{OUT} \cong \Delta I_L \left(ESR + \frac{1}{8fC_{OUT}}\right)$$

Where f = operating frequency, C_{OUT} = output capacitance and ΔI_L = ripple current in the inductor. For a fixed output voltage, the output ripple is highest at maximum input voltage since ΔI_L increases with input voltage.

Aluminum electrolytic and dry tantalum capacitors are both available in surface mount configurations. In the case of tantalum, it is critical that the capacitors are surge tested for use in switching power supplies. An excellent choice is the AVX TPS series of surface mount tantalum. These are specially constructed and tested for low ESR so they give the lowest ESR for a given volume. The Table 1 shows the suggested capacitors for CIN and COUT.

Efficiency Considerations

The efficiency of a switching regulator is equal to the output power divided by the input power times 100%. It is often useful to analyze individual losses to determine what is limiting the efficiency and which change would produce the most improvement. Efficiency can be expressed as: Efficiency = 100% - (L1+ L2+ L3+ ...) where L1, L2, etc. are the individual losses as a percentage of input power. Although all dissipative elements in the circuit produce losses, two main sources usually account for most of the losses: VIN quiescent current and I^2R losses. The VIN quiescent current loss dominates the efficiency loss at very low load currents whereas the I^2R loss dominates the efficiency loss at medium to high load currents. In a typical efficiency plot, the efficiency curve at very low load currents can be misleading since the actual power lost is of no consequence.

1. The VIN quiescent current is due to two components: the DC bias current as given in the electrical characteristics and the internal main switch and synchronous switch gate charge currents. The gate charge current results from switching the gate capacitance of the internal power MOSFET switches. Each time the gate is switched from high to low to high again, a packet of charge $\triangle Q$ moves from VIN to ground. The resulting $\triangle Q/\triangle t$ is the current out of VIN that is typically larger than the DC bias current. In continuous mode, $I_{GATECHG} = f (Q_T+Q_B)$ where Q_T and Q_B are the gate charges of the internal top and bottom switches. Both the DC bias and gate charge losses are proportional to VIN and thus their effects will be more pronounced at higher supply voltages.

2. I^2R losses are calculated from the resistances of the internal switches, R_{SW} and external inductor R_L. In continuous mode the average output current flowing through inductor L is “chopped” between the main switch and the synchronous switch. Thus, the series resistance looking into the SW pin is a function of both top and bottom MOSFET $R_{DS(ON)}$ and the duty cycle (DC) as follows: $R_{SW} = R_{DS(ON)TOP}$ x DC + $R_{DS(ON)BOT}$ x (1-DC) The $R_{DS(ON)}$ for both the top and bottom MOSFETs can be obtained from the Typical Performance Characteristics curves. Thus, to obtain I^2R losses, simply add R_{SW} to R_L and multiply the result by the square of the average output current. Other losses including CIN and COUT ESR dissipative losses and inductor core losses generally account for less than 2% of the total loss.

Board Layout Suggestions

When laying out the printed circuit board, the following checklist should be used to ensure proper operation of the HX1009-AMH. Check the following in your layout:

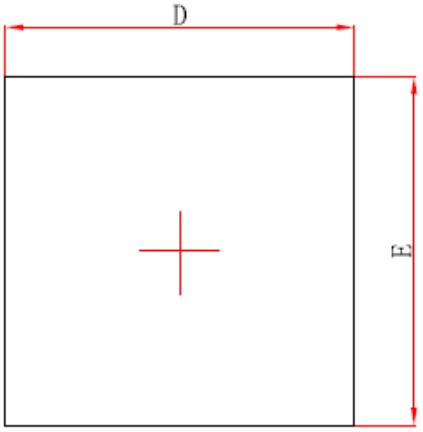
1. The power traces, consisting of the GND trace, the SW trace and the V_{IN} trace should be kept short, direct and wide.
2. Put the input capacitor as close as possible to the device pins (VIN and GND).
3. SW node is with high frequency voltage swing and should be kept small area. Keep analog components away from SW node to prevent stray capacitive noise pick-up.
4. Connect all analog grounds to a command node and then connect the command node to the power ground behind the output capacitors.

Table 1: Suggested Capacitors for C_{IN} and C_{OUT}

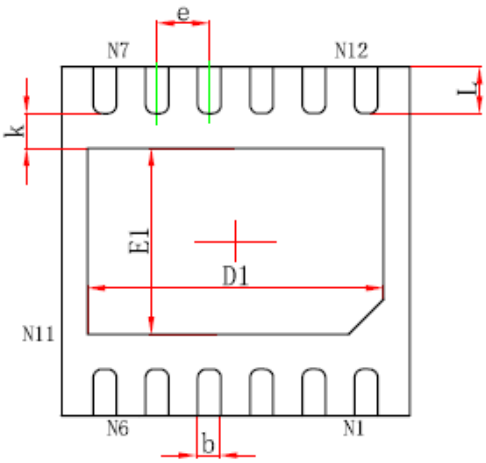
Component Supplier	Part No.	Capacitance (uF)	Case Size
TDK	C2012JB0J106M	10	0805
MURATA	GRM219R60J106ME19	10	0805
TAIYO YUDEN	JMK107BJ106MA	10	0603

Packaging Information

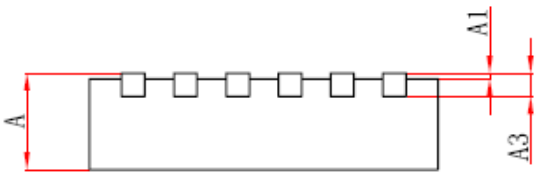
DFN3*3-12L Package Outline Dimension



Top View



Bottom View



Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700/0.800	0.800/0.900	0.028/0.031	0.031/0.035
A1	0.000	0.050	0.000	0.002
A3	0.203REF		0.008REF	
D	2.924	3.076	0.115	0.121
E	2.924	3.076	0.115	0.121
D1	2.450	2.650	0.096	0.104
E1	1.500	1.700	0.059	0.067
k	0.200MIN		0.008MIN	
b	0.150	0.250	0.006	0.010
e	0.450TYP.		0.018TYP.	
L	0.324	0.476	0.013	0.019

Subject changes without notice.

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